



40V 175°C DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

| BVDSS | R _{DS(ON)} Max | I _D Max T _C = +25°C |
|-------|--|--|
| 40V | 12.3m Ω @ V _{GS} = 10V | 46.2A |
| | $17.5 \text{m}\Omega$ @ V _{GS} = 4.5V | 38.7A |

Description and Applications

This new generation MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- **Power Management Functions**
- DC-DC Converters

Features and Benefits

- Rated to +175°C Ideal for High Ambient Temperature **Environments**
- 100% Unclamped Inductive Switching, Test in Production-Ensures More Reliable and Robust End Application
- High Conversion Efficiency
- Low R_{DS(ON)} Minimizes On State Losses
- Low Input Capacitance
- Fast Switching Speed
- Wettable Flank for Improved Optical Inspection
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/
- An Automotive-Compliant Part is Available Under Separate Datasheet (DMTH4008LPDWQ)

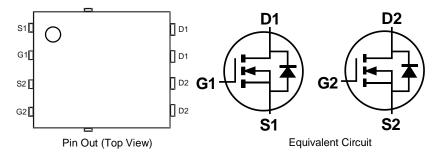
Mechanical Data

- Case: PowerDI®5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.097 grams (Approximate)

PowerDI5060-8/SWP (Type UXD)







Ordering Information (Note 4)

| Part Number | Case | Packaging |
|-----------------|------------------------------|-------------------|
| DMTH4008LPDW-13 | PowerDI5060-8/SWP (Type UXD) | 2,500/Tape & Reel |

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See http://www.diodes.com/quality/lead_free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information

Document number: DS42438 Rev. 1 - 2



) | | = Manufacturer's Marking TH4008LDW = Product Type Marking Code YYWW or YYWW = Date Code Marking YY or \overline{YY} = Year (ex: 20 = 2020) WW = Week (01 to 53)

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Maximum Ratings (@TA = +25°C, unless otherwise specified.)

| Characteristic | | Symbol | Value | Unit |
|---|---|-----------------|--------------|------|
| Drain-Source Voltage | V _{DSS} | 40 | V | |
| Gate-Source Voltage | Vgss | ±20 | V | |
| Continuous Drain Current (Note 5) | T _A = +25°C T _A = +100°C | lD | 10.0 7.1 | А |
| Continuous Drain Current (Note 6) | $T_{C} = +25^{\circ}C$ $T_{C} = +100^{\circ}C$ | I _D | 46.2 32.7 | А |
| Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%) | Ірм | 184 | Α | |
| Maximum Continuous Body Diode Forward Current (Note 6) | Is | 43.7 | Α | |
| Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%) | | I _{SM} | 184 | Α |
| Avalanche Current, L = 0.1mH | | las | 23.1 | Α |
| Avalanche Energy, L = 0.1mH | | Eas | 26.6 | mJ |

Thermal Characteristics

| Characteristic | | Symbol | Value | Unit |
|---|--|----------|-------------|------|
| Total Power Dissipation (Note 5) T _A = +25°C | | PD | 2.67 | W |
| Thermal Resistance, Junction to Ambient (Note 5) | | Reja | 56.6 | °C/W |
| Total Power Dissipation (Note 6) $T_C = +25^{\circ}C$ | | PD | 39.4 | W |
| Thermal Resistance, Junction to Case (Note 6) | | Rejc | 3.8 | °C/W |
| Operating and Storage Temperature Range | | TJ, TSTG | -55 to +175 | °C |

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

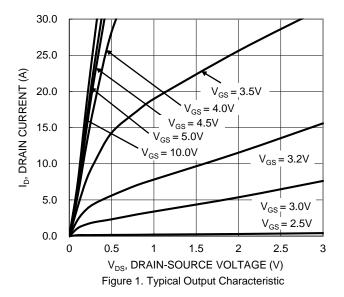
| Characteristic | Symbol | Min | Тур | Max | Unit | Test Condition | |
|--|---------------------|-----|------|------|------|---|--|
| OFF CHARACTERISTICS (Note 7) | | | | | | | |
| Drain-Source Breakdown Voltage | | 40 | _ | _ | V | $V_{GS} = 0V, I_{D} = 250\mu A$ | |
| Zero Gate Voltage Drain Current | IDSS | _ | _ | 1 | μΑ | V _{DS} = 32V, V _{GS} = 0V | |
| Gate-Source Leakage | | _ | _ | ±100 | nA | $V_{GS} = \pm 20V, V_{DS} = 0V$ | |
| ON CHARACTERISTICS (Note 7) | | | | | | | |
| Gate Threshold Voltage | V _{GS(TH)} | 1.2 | 1.88 | 2.3 | V | $V_{DS} = V_{GS}$, $I_D = 250\mu A$ | |
| Static Drain-Source On-Resistance | - | _ | 9.5 | 12.3 | mΩ | Vgs = 10V, ID = 20A | |
| Static Dialit-Source Off-Nesistance | RDS(ON) | _ | 11.9 | 17.5 | mΩ | Vgs = 4.5V, ID = 10A | |
| Diode Forward Voltage | V _{SD} | _ | 0.9 | 1.2 | V | $V_{GS} = 0V, I_{S} = 20A$ | |
| DYNAMIC CHARACTERISTICS (Note 8) | | | | | | | |
| Input Capacitance | Ciss | _ | 881 | _ | pF | \ | |
| Output Capacitance | Coss | _ | 496 | _ | pF | V _{DS} = 20V, V _{GS} = 0V, f = 1MHz | |
| Reverse Transfer Capacitance | Crss | _ | 19.5 | _ | pF | | |
| Gate Resistance | Rg | _ | 2.06 | _ | Ω | $V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$ | |
| Total Gate Charge (V _{GS} = 10V) | Qg | _ | 12.3 | _ | nC | | |
| Total Gate Charge (V _{GS} = 4.5V) | Qg | _ | 5.8 | _ | nC | \/ 20\/ I- 20A | |
| Gate-Source Charge | Qgs | _ | 2.6 | _ | nC | $V_{DS} = 20V, I_{D} = 20A$ | |
| Gate-Drain Charge | Q _{gd} | _ | 1.6 | _ | nC | 1 | |
| Turn-On Delay Time | t _{D(ON)} | _ | 3.82 | _ | ns | | |
| Turn-On Rise Time | t _R | _ | 4.76 | _ | ns | $V_{DD} = 20V, V_{GS} = 10V,$ $R_g = 3\Omega, I_D = 20A$ | |
| Turn-Off Delay Time | tD(OFF) | _ | 12.6 | _ | ns | | |
| Turn-Off Fall Time | tF | _ | 4.83 | _ | ns | | |
| Body Diode Reverse Recovery Time | t _{RR} | _ | 31.9 | _ | ns | I_ 20A di/dt 100A/vo | |
| Body Diode Reverse Recovery Charge | Q _{RR} | _ | 25.0 | _ | nC | $I_F = 20A$, di/dt = 100A/ μ s | |

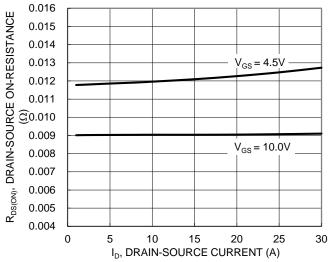
5. Device mounted on FR-4 substrate PC board, 2oz. copper, with thermal bias to bottom layer 1inch square copper plate.

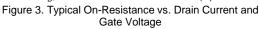
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Thermal resistance from junction to soldering point (on the exposed drain pad).
Short duration pulse test used to minimize self-heating effect.
Guaranteed by design. Not subject to product testing.









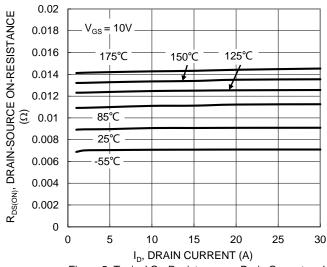
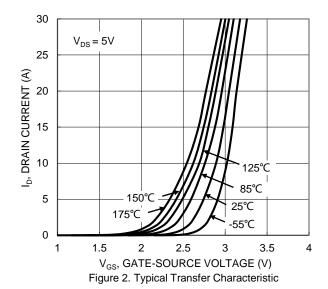
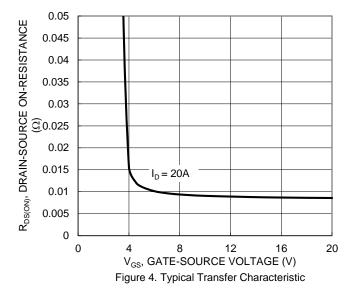


Figure 5. Typical On-Resistance vs. Drain Current and Temperature





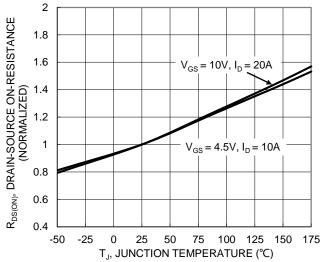


Figure 6. On-Resistance Variation with Temperature



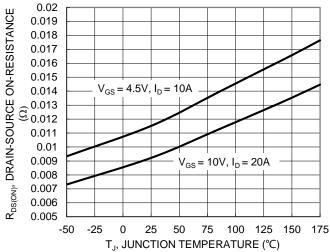
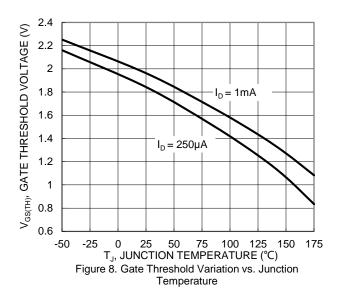
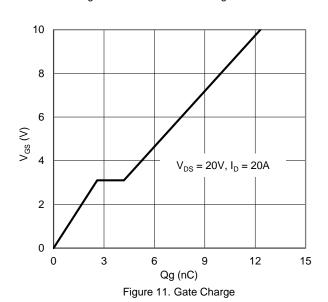


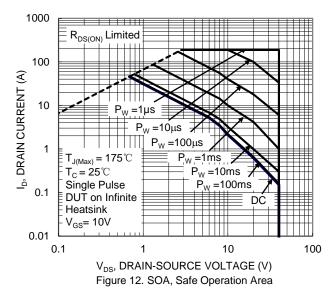
Figure 7. On-Resistance Variation with Temperature



30 $V_{GS} = 0V$ 25 Is, SOURCE CURRENT (A) 20 15 $T_A = 85^{\circ}C$ T_A = 125°C 10 T_A = 150°C 5 T_A = 25°C $T_A = -55$ °C 0 0 0.6 V_{SD}, SOURCE-DRAIN VOLTAGE (V) Figure 9. Diode Forward Voltage vs. Current



10000 f=1MHz C_T, JUNCTION CAPACITANCE (pF) C_{iss} 1000 Coss 100 10 0 5 10 15 20 25 30 35 40 V_{DS} , DRAIN-SOURCE VOLTAGE (V) Figure 10. Typical Junction Capacitance





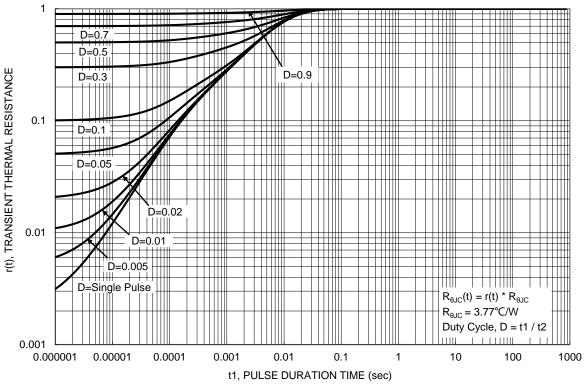


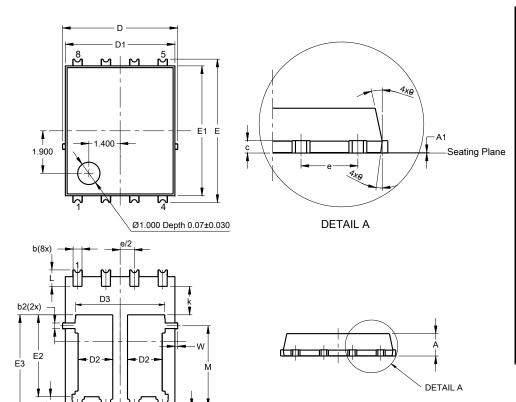
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8/SWP (Type UXD)

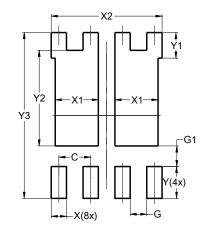


| PowerDI5060-8/SWP (Type UXD) | | | | |
|---------------------------------|-------|---------|-------|--|
| Dim | Min | Max | Тур | |
| Α | 0.90 | 1.10 | 1.00 | |
| A1 | 0.00 | 0.05 | | |
| b | 0.30 | 0.50 | 0.41 | |
| b2 | 0.20 | 0.35 | 0.25 | |
| b4 | (|).25REF | | |
| С | 0.230 | 0.330 | 0.277 | |
| D | - | .15 BS0 | _ | |
| D1 | 4.70 | 5.10 | 4.90 | |
| D2 | 1.46 | 1.66 | 1.55 | |
| D3 | 3.78 | 4.18 | 3.98 | |
| Е | 6 | .40 BS0 | 3 | |
| E1 | 5.60 | 6.00 | 5.80 | |
| E2 | 3.46 | 3.86 | 3.66 | |
| E2a | 4.195 | 4.595 | 4.395 | |
| е | 1 | .27BSC | ; | |
| k | 1.05 | | | |
| L | 0.635 | 0.835 | 0.735 | |
| La | 0.635 | 0.835 | 0.735 | |
| L1 | 0.200 | 0.400 | 0.300 | |
| М | 3.205 | 4.005 | 3.605 | |
| W | 0.025 | 0.225 | 0.125 | |
| θ | 10° | 12° | 11° | |
| θ1 | 6° | 8° | 7° | |
| All Dimensions in mm | | | | |

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8/SWP (Type UXD)



| Dimensions | Value (in mm) | | |
|------------|------------------|--|--|
| С | 1.270 | | |
| G | 0.660 | | |
| G1 | 0.820 | | |
| X | 0.610 | | |
| X1 | 1.720 | | |
| X2 | 4.420 | | |
| Y | 1.270 | | |
| Y1 | 1.020 | | |
| Y2 | 3.810 | | |
| Y3 | 6.610 | | |



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